BAS19LT1G, BAS20LT1G, BAS21LT1G, BAS21DW5T1G

High Voltage Switching Diode

ON Semiconductor®

http://onsemi.com

HIGH VOLTAGE SWITCHING DIODE

Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

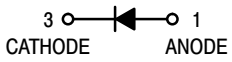
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage BAS19 BAS20 BAS21	V_R	 120 200 250	Vdc
Repetitive Peak Reverse Voltage BAS19 BAS20 BAS21	V_{RRM}	 120 200 250	Vdc
Continuous Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
Power Dissipation (Note 1)	P_D	385	mW
Electrostatic Discharge	ESD	HM < 500 MM < 400	V V

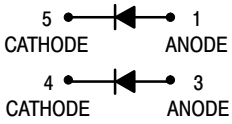
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Mounted on FR−5 Board = 1.0 x 0.75 x 0.062 in.

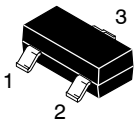
SOT−23



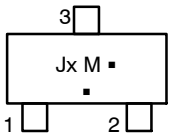
SC−88A



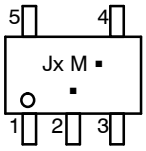
MARKING DIAGRAMS



SOT−23 (TO−236)
CASE 318
STYLE 8



SC−88A (SOT−353)
CASE 419A



x = P, R, or S
P = BAS19LT1
R = BAS20LT1
S = BAS21LT1 or BAS21DW5T1
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon the manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

THERMAL CHARACTERISTICS (SOT−23)

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 2) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction−to−Ambient (SOT−23)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 3) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

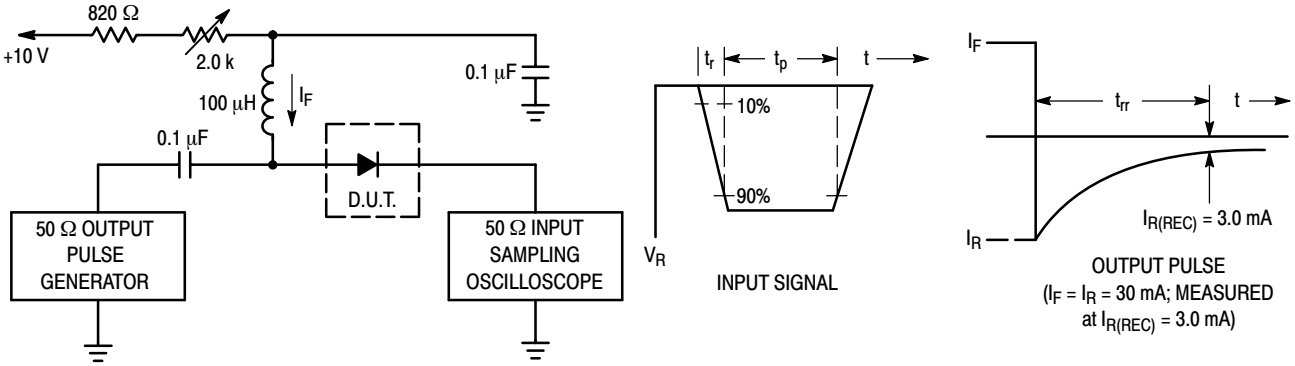
THERMAL CHARACTERISTICS (SC−88A)

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P_D	385	mW
Thermal Resistance − Junction−to−Ambient Derate Above 25°C	$R_{\theta JA}$	328 3.0	°C/W mW/°C
Maximum Junction Temperature	T_{Jmax}	150	°C
Operating Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

2. FR−5 = 1.0 × 0.75 × 0.062 in.
3. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.
4. Mounted on FR−5 Board = 1.0 x 0.75 x 0.062 in.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
Reverse Voltage Leakage Current		I_R			μAdc
(V_R = 100 Vdc)	BAS19		−	0.1	
(V_R = 150 Vdc)	BAS20		−	0.1	
(V_R = 200 Vdc)	BAS21		−	0.1	
(V_R = 100 Vdc, T_J = 150°C)	BAS19		−	100	
(V_R = 150 Vdc, T_J = 150°C)	BAS20		−	100	
(V_R = 200 Vdc, T_J = 150°C)	BAS21		−	100	
Reverse Breakdown Voltage		$V_{(BR)}$			Vdc
(I_{BR} = 100 μAdc)	BAS19		120	−	
(I_{BR} = 100 μAdc)	BAS20		200	−	
(I_{BR} = 100 μAdc)	BAS21		250	−	
Forward Voltage		V_F			Vdc
(I_F = 100 mAdc)			−	1.0	
(I_F = 200 mAdc)			−	1.25	
Diode Capacitance (V_R = 0, f = 1.0 MHz)		C_D	−	5.0	pF
Reverse Recovery Time (I_F = I_R = 30 mAdc, $I_{R(REC)}$ = 3.0 mAdc, R_L = 100)		t_{rr}	−	50	ns



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

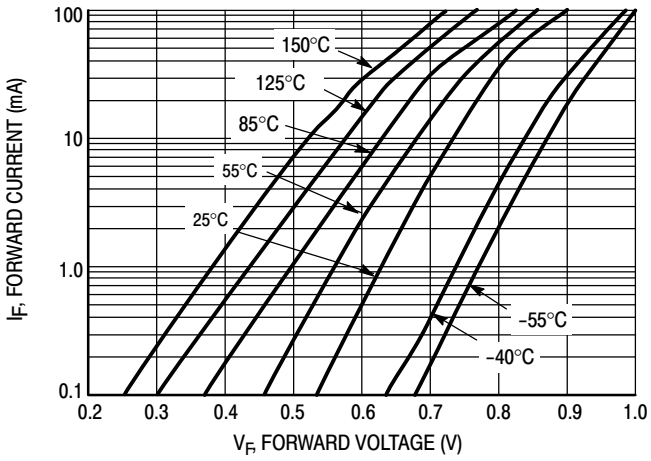


Figure 2. V_F vs. I_F

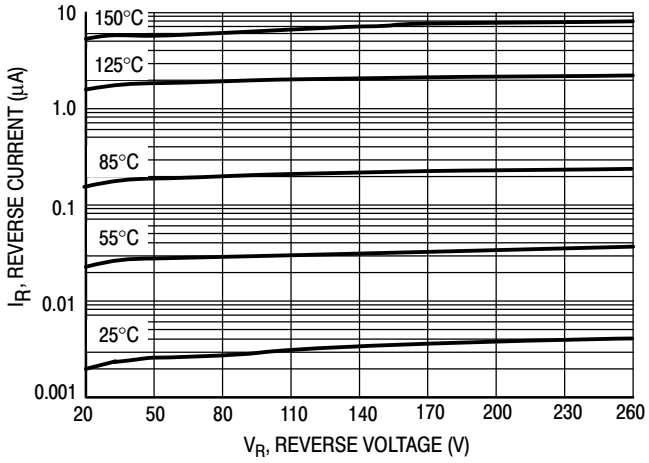


Figure 3. I_R vs. V_R

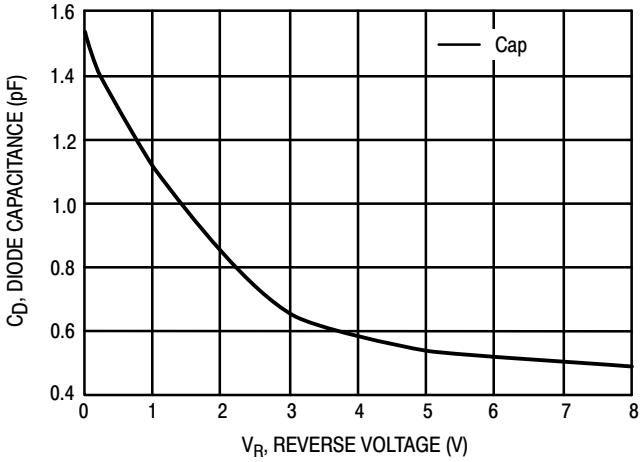


Figure 4. Capacitance

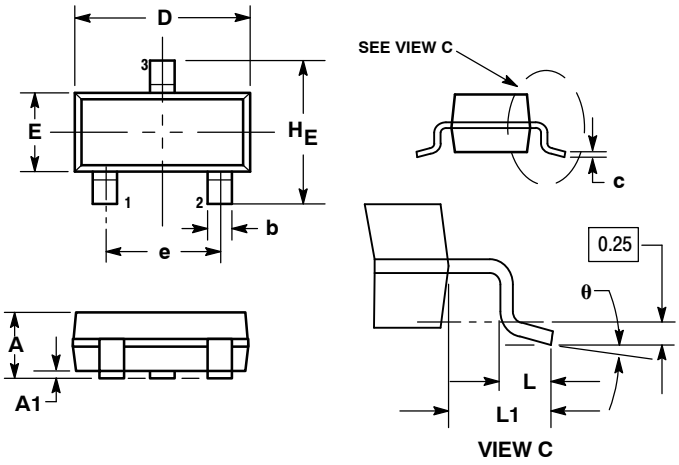
ORDERING INFORMATION

Device	Package	Shipping†
BAS19LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS19LT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel
BAS20LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS21LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAS21LT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel
BAS21DW5T1G	SC−88A (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AN

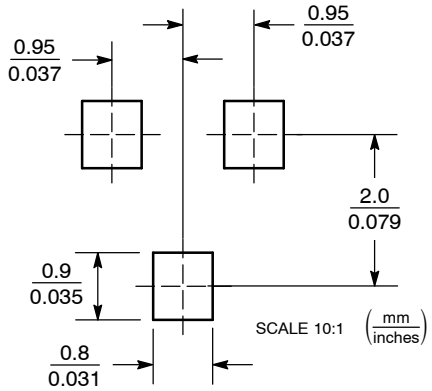


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01 THRU −07 AND −09 OBSOLETE, NEW STANDARD 318−08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

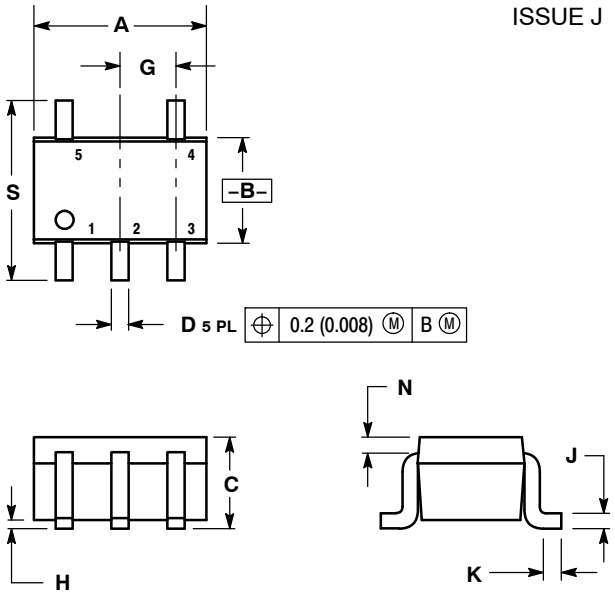
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

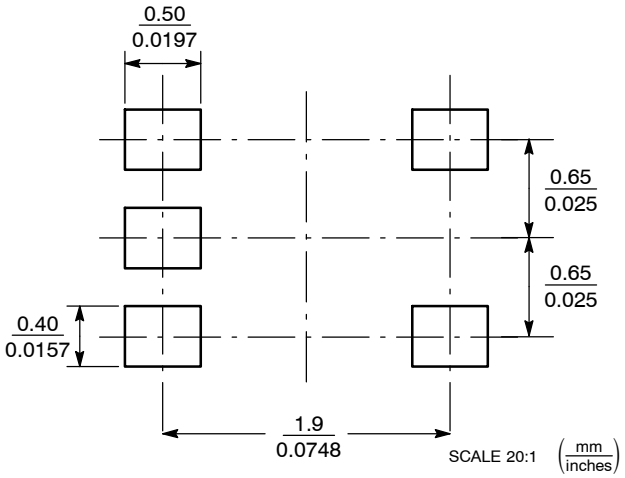
SC−88A, SOT−353, SC−70
CASE 419A−02
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

BAS19LT1/D